

EE247

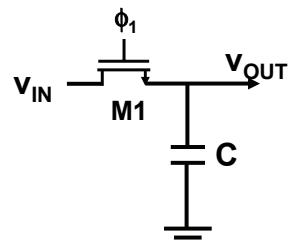
Lecture 17

ADC Converters

- Sampling (continued)
 - Sampling switch considerations
 - Clock voltage boosters
 - Sampling switch charge injection & clock feedthrough
 - Complementary switch
 - Use of dummy device
 - Bottom-plate switching
- Track & hold
 - T/H circuits
 - T/H combined with summing/difference function
 - T/H circuit incorporating gain & offset cancellation

Practical Sampling Summary So Far!

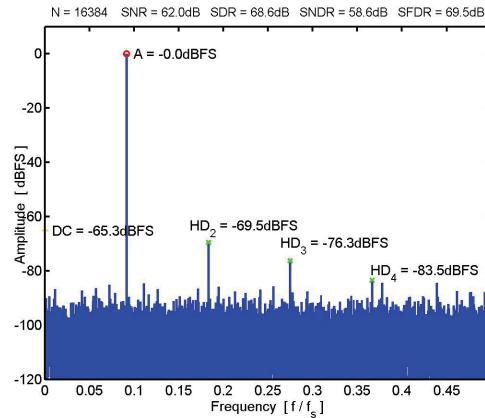
- kT/C noise
$$C \geq 12k_B T \frac{2^{2B}}{V_{FS}^2}$$
- Finite R_{sw} → limited bandwidth
$$R \ll \frac{0.72}{B f_s C}$$
- $g_{sw} = f(V_{in})$ → distortion



- $$g_{ON} = g_o \left(1 - \frac{V_{in}}{V_{DD} - V_{th}} \right) \quad \text{for} \quad g_o = \mu C_{ox} \frac{W}{L} (V_{DD} - V_{th})$$
- Allowing long enough settling time → reduce distortion due to sw non-linear behavior

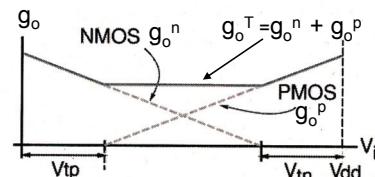
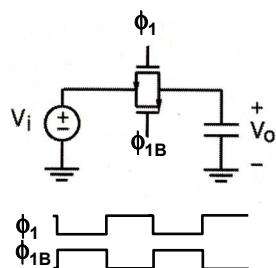
Signal Distortion Due to Sampling Switch Nonlinearity

- SFDR → sensitive to sampling distortion - improve linearity by:
 - Larger V_{DD}/V_{FS}
 - Higher sampling bandwidth
- Solutions:
 - Overdesign → Larger switches
 - Issue:
 - Increased switch charge injection
 - Increased nonlinear S & D junction cap.
 - Maximize V_{DD}/V_{FS}
 - Decreased dynamic range if V_{DD} const.
 - Complementary switch?
 - Constant & max. $V_{GS} \neq f(V_{in})$?



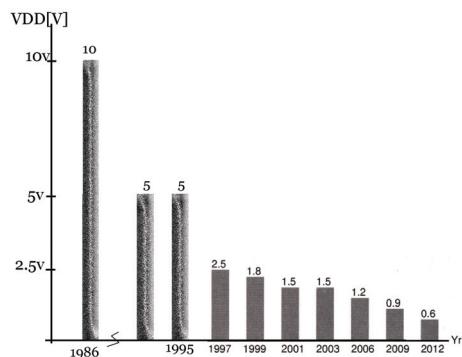
$$10\text{bit ADC} \quad T_s/\tau = 20 \\ V_{DD} - V_{th} = 2V \quad V_{FS} = 1V$$

Sampling Use of Complementary Switches



- Complementary n & p switch advantages:
 - ✓ Increase in the overall conductance → lower time constant
 - ✓ Linearize the switch conductance for the range $|V_{th}^p| < V_{in} < V_{dd} - |V_{th}^n|$

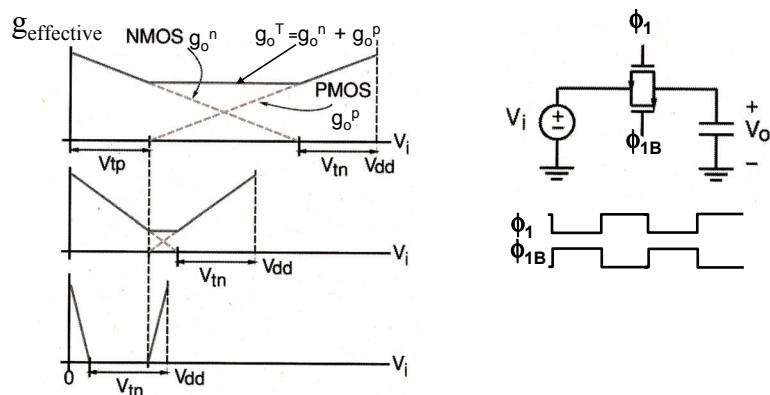
Complementary Switch Issues Supply Voltage Evolution



- Supply voltage has scaled down with technology scaling
- Threshold voltages do not scale accordingly

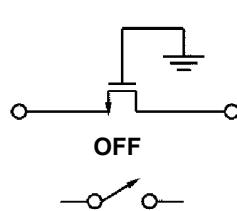
Ref: A. Abo et al, "A 1.5-V, 10-bit, 14.3-MS/s CMOS Pipeline Analog-to-Digital Converter," JSSC May 1999, pp. 599.

Complementary Switch Effect of Supply Voltage Scaling

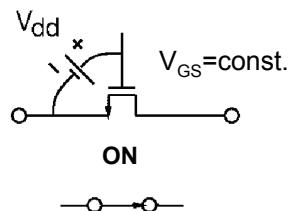


- As supply voltage scales down input voltage range for constant g_o shrinks
→ Complementary switch not effective when V_{DD} becomes comparable to $2 \times V_{th}$

Boosted & Constant V_{GS} Sampling

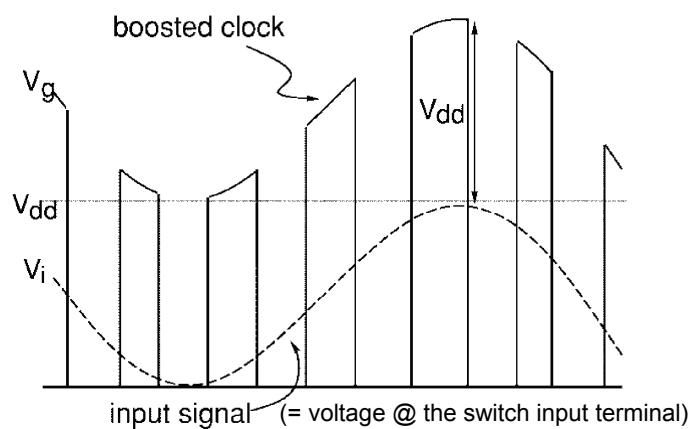


- Gate voltage V_{GS} =low
 - Device off
 - Beware of signal feedthrough due to parasitic capacitors

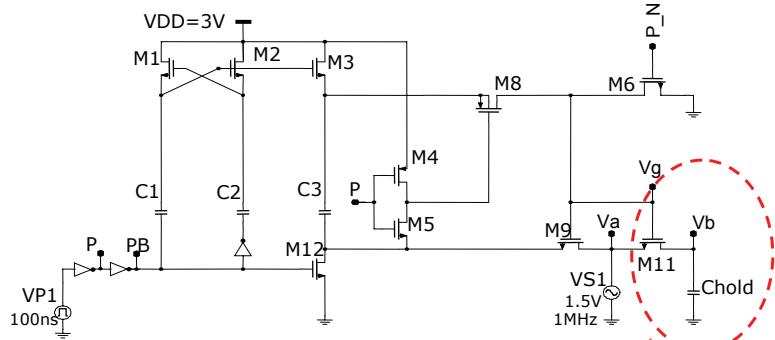


- Increase gate overdrive voltage as much as possible + keep V_{GS} constant
 - Switch overdrive voltage independent of signal level
 - Error due to finite R_{ON} linear (to 1st order)
 - Lower R_{on} \rightarrow lower time constant

Constant V_{GS} Sampling



Constant V_{GS} Sampling Circuit



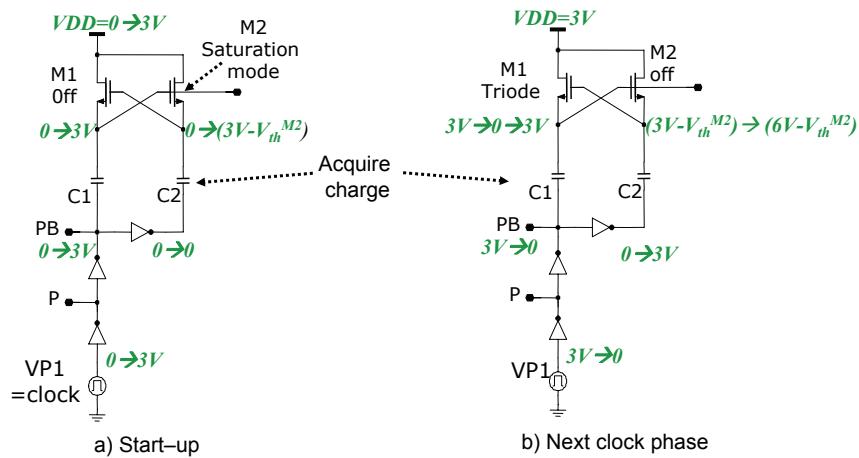
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Clock Voltage Doubler

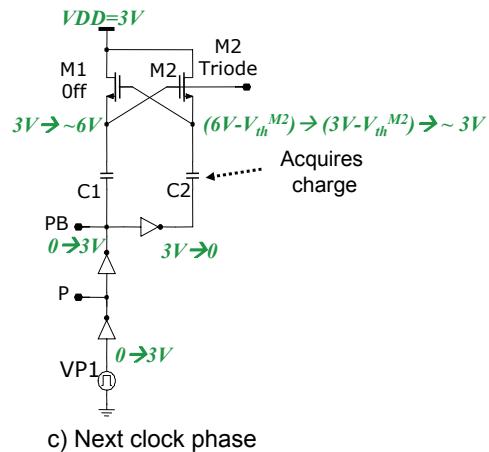


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Clock Voltage Doubler

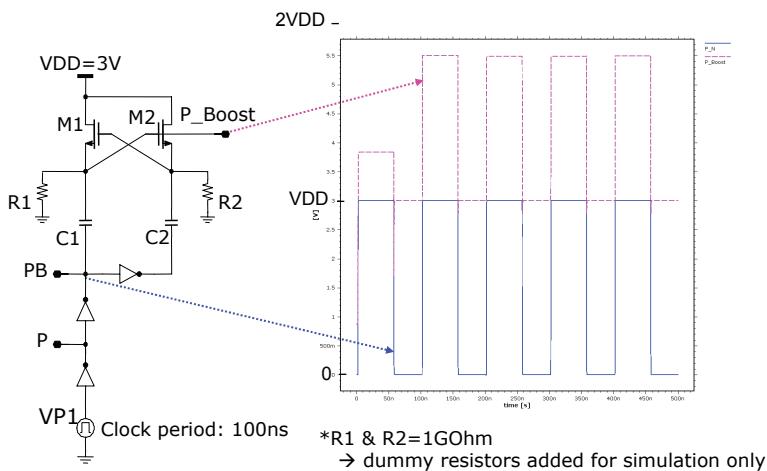


c) Next clock phase

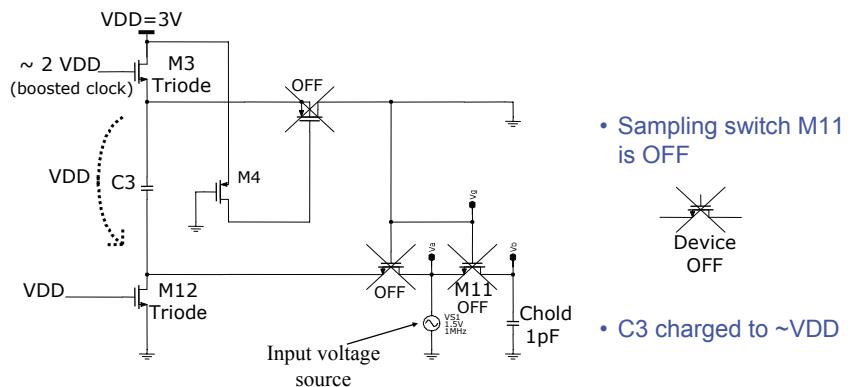
- Both C1 & C2 → charged to VDD after 1.5 clock cycle

- Note that bottom plate of C1 & C2 is either 0 or VDD while top plates are at VDD or 2VDD

Clock Voltage Doubler



Constant V_{GS} Sampler: Φ Low

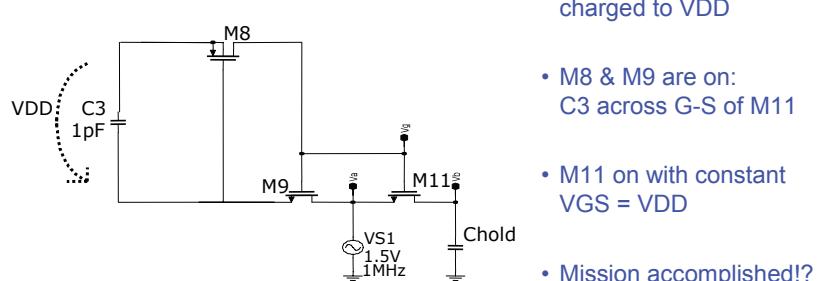


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Constant V_{GS} Sampler: Φ High

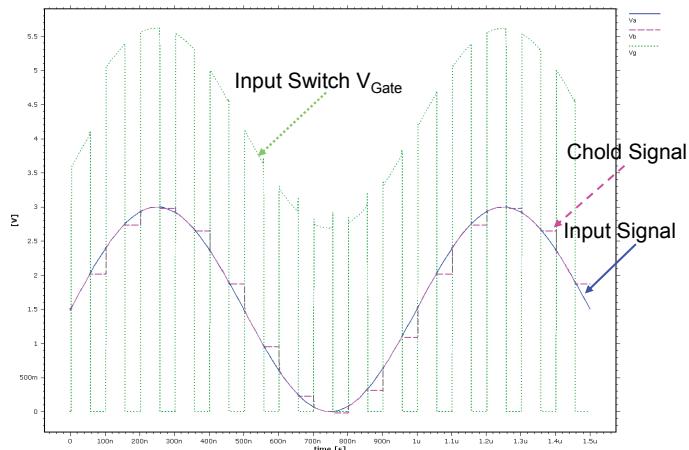


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Constant V_{GS} Sampling

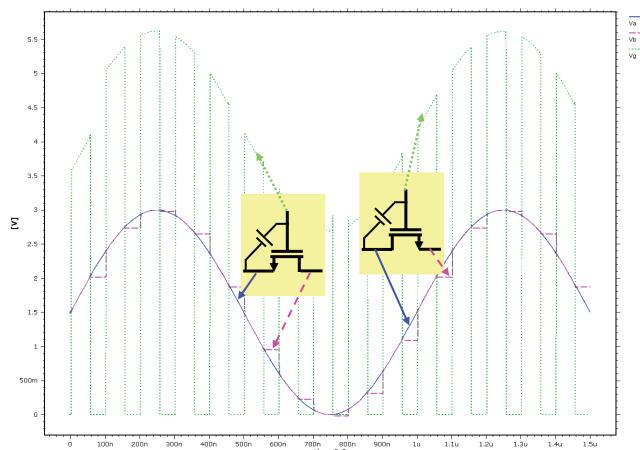


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Constant V_{GS} Sampling?



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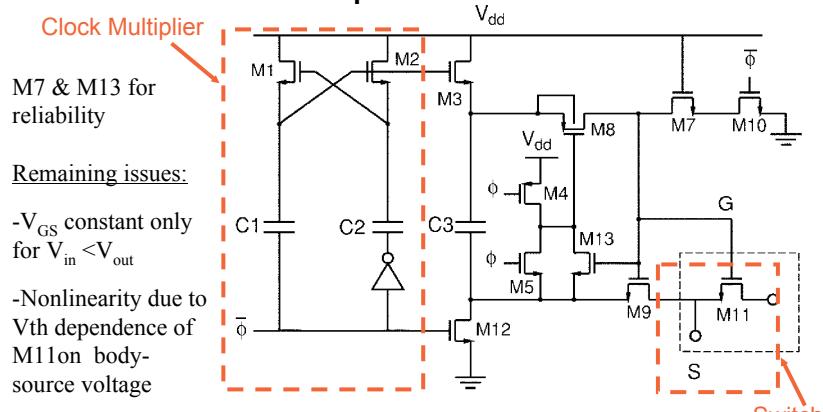
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Constant V_{GS} Sampling?



- During the time period: $V_{in} < V_{out}$
 $\rightarrow V_{GS} = \text{constant} = V_{DD}$
 - Larger $V_{GS} - V_{th}$ compared to no boost
 - $V_{GS} = \text{cte}$ and not a function of input voltage
 \rightarrow Significant linearity improvement
- During the time period: $V_{in} > V_{out}$:
 $\rightarrow V_{GS} = V_{DD} - IR$
 - Larger $V_{GS} - V_{th}$ compared to no boost
 - V_{GS} is a function of IR and hence input voltage
 \rightarrow Linearity improvement not as pronounced as for $V_{in} < V_{out}$

Boosted Clock Sampling Complete Circuit



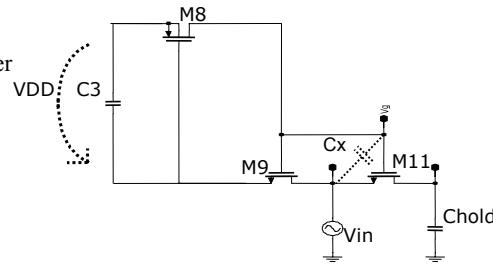
Ref: A. Abo et al, "A 1.5-V, 10-bit, 14.3-MS/s CMOS Pipeline Analog-to-Digital Converter," JSSC May 1999, pp. 599.

Boosted Clock Sampling Design Consideration

Choice of value for C3:

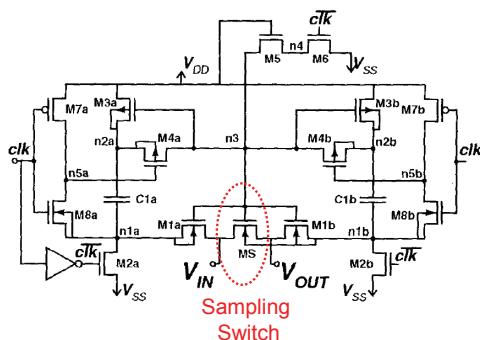
- C3 too large → large charging current → large dynamic power dissipation

- C3 too small →
 $V_{gate}-V_s = V_{DD} \cdot C_3 / (C_3 + C_x)$
 → Loss of VGS due to low ratio of C_x/C_3
 C_x includes C_{GS} of M11 plus all other parasitics caps....



Ref: A. Abo et al, "A 1.5-V, 10-bit, 14.3-MS/s CMOS Pipeline Analog-to-Digital Converter," JSSC May 1999, pp. 599.

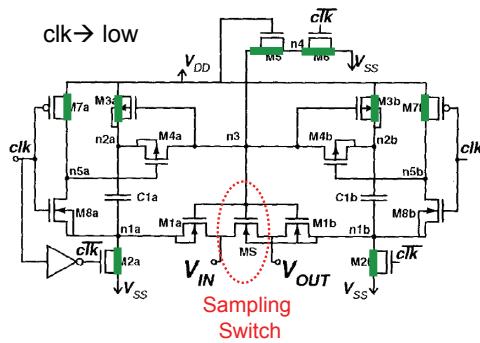
Advanced Clock Boosting Technique



Ref: M. Waltari et al., "A self-calibrated pipeline ADC with 200MHz IF-sampling frontend," ISSCC 2002, Dig. Tech. Papers, pp. 314

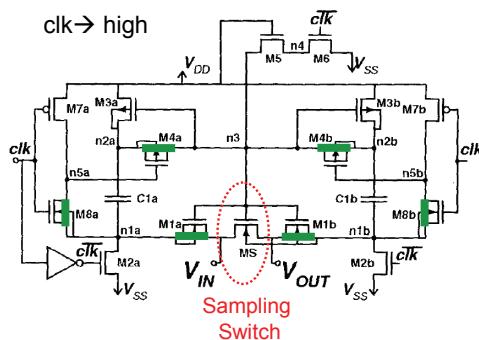
Two floating voltages sources generated and connected to Gate and S & D

Advanced Clock Boosting Technique



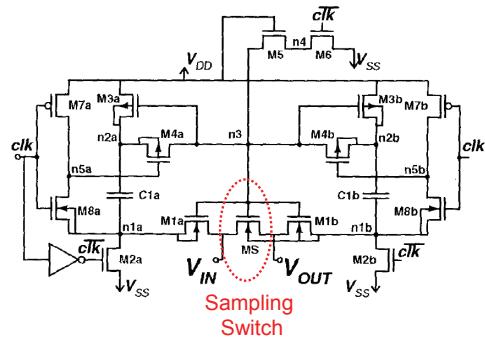
- $\bar{clk} \rightarrow \text{low}$
 - Capacitors $C1a$ & $C1b \rightarrow$ charged to V_{DD}
 - MS \rightarrow off
 - Hold mode

Advanced Clock Boosting Technique



- $clk \rightarrow \text{high}$
 - Top plate of $C1a$ & $C1b$ connected to gate of sampling switch
 - Bottom plate of $C1a$ connected to V_{IN}
 - Bottom plate of $C1b$ connected to V_{OUT}
 - VGS & VGD of MS both @ V_{DD} & ac signal on G of MS \rightarrow average of V_{IN} & V_{OUT}

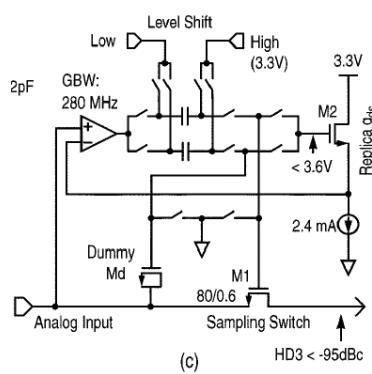
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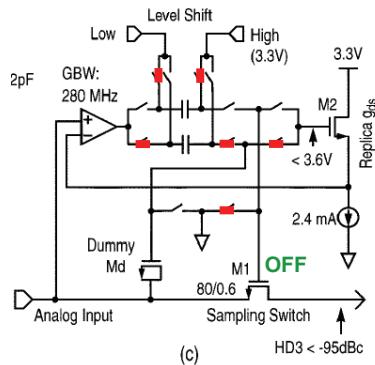
- Gate tracks *average* of input and output, reduces effect of I·R drop at high frequencies
- Bulk also tracks signal \Rightarrow reduced body effect (technology used allows connecting bulk to S)
- Reported measured SFDR = 76.5dB at $f_{in}=200\text{MHz}$

Constant Conductance Switch



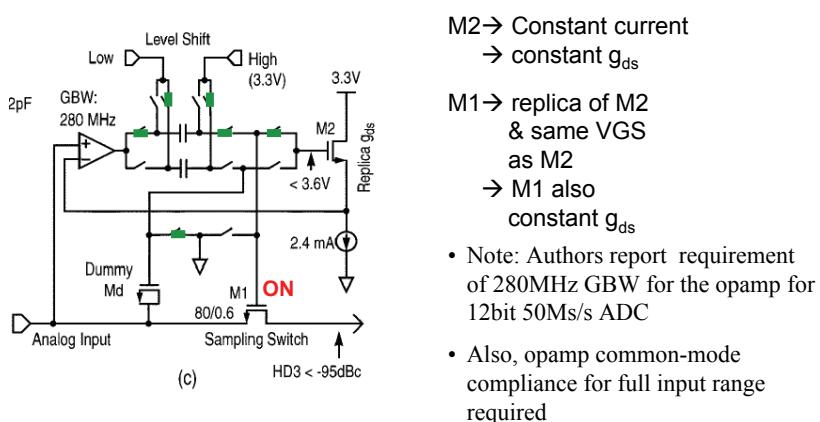
Ref: H. Pan et al., "A 3.3-V 12-b 50-MS/s A/D converter in 0.6μm CMOS with over 80-dB SFDR," IEEE J. Solid-State Circuits, pp. 1769-1780, Dec. 2000

Constant Conductance Switch



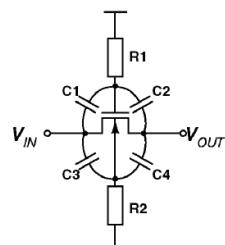
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Constant Conductance Switch

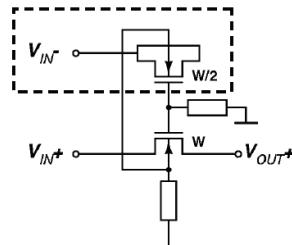


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Switch Off-Mode Feedthrough Cancellation



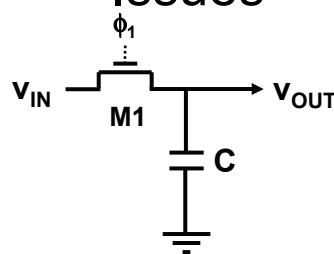
High-pass feedthrough paths past an open switch



Feedthrough cancellation with a dummy switch

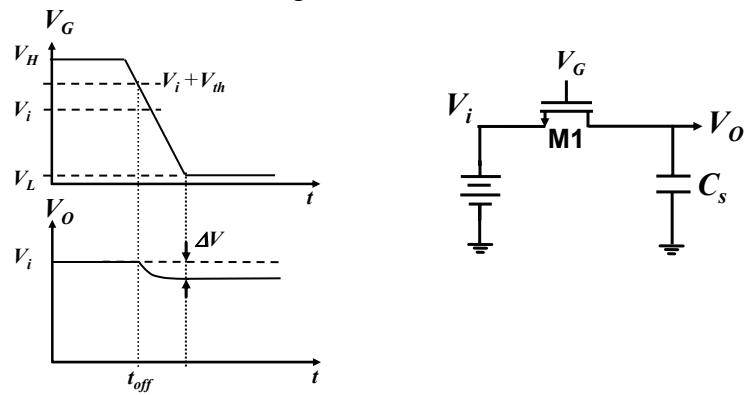
Ref: M. Waltari et al., "A self-calibrated pipeline ADC with 200MHz IF-sampling frontend," ISSCC 2002, Dig. Techn. Papers, pp. 314

Practical Sampling Issues



- Switch induced noise due to M1 finite channel resistance
- Clock jitter
- Finite R_{sw} → limited bandwidth → finite acquisition time
- $R_{sw} = f(V_{in})$ → distortion
- Switch charge injection & clock feedthrough

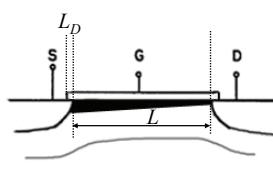
Sampling Switch Charge Injection & Clock Feedthrough Switching from Track to Hold



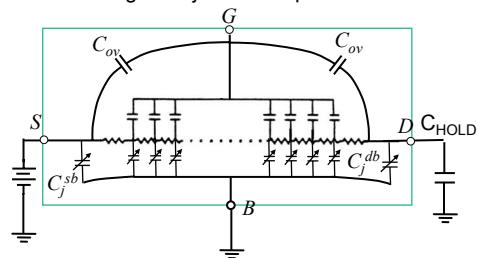
- First assume V_i is a DC voltage
- When switch turns off \rightarrow offset voltage induced on C_s
- Why ?

Sampling Switch Charge Injection

MOS xtor operating in triode region
Cross section view

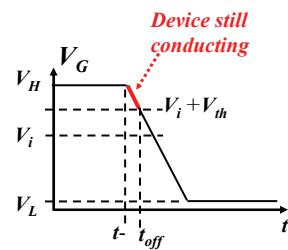
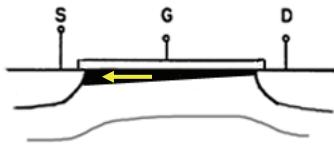


Distributed channel resistance &
gate & junction capacitances



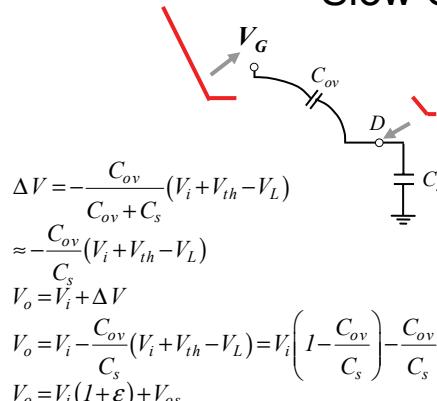
- Channel \rightarrow distributed RC network formed between G,S, and D
- Channel to substrate junction capacitance \rightarrow distributed & voltage dependant
- Drain/Source junction capacitors to substrate \rightarrow voltage dependant
- Over-lap capacitance $C_{ov} = L_D \times W \times C_{ox}$ associated with G-S & G-D overlap

Switch Charge Injection Slow Clock

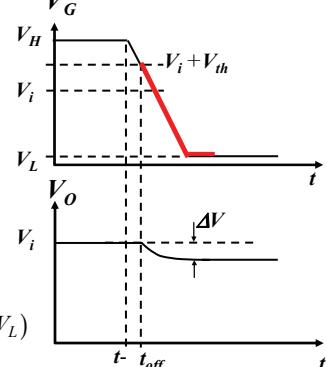


- Slow clock \rightarrow clock fall time $>>$ device speed
 \rightarrow During the period (t - to t_{off}) current in channel discharges channel charge into low impedance signal source
- Only source of error \rightarrow Clock feedthrough from C_{ov} to C_s

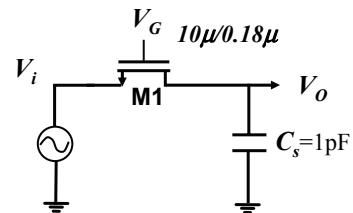
Switch Clock Feedthrough Slow Clock



$$\text{where } \epsilon = -\frac{C_{ov}}{C_s}; V_{os} = -\frac{C_{ov}}{C_s}(V_{th} - V_L)$$



Switch Charge Injection & Clock Feedthrough Slow Clock- Example

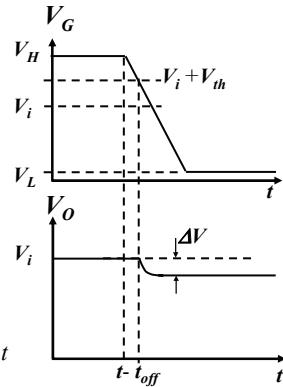


$$C'_{ov} = 0.1 fF/\mu \quad C_{ox} = 9 fF/\mu^2 \quad V_{th} = 0.4V \quad V_L = 0$$

$$\epsilon = -\frac{C_{ov}}{C_s} = -\frac{10\mu \times 0.1 fF/\mu}{1 pF} = -0.1\%$$

Allowing $\epsilon = 1/2LSB \rightarrow ADC resolution \sim 9bit$

$$V_{os} = -\frac{C_{ov}}{C_s} (V_{th} - V_L) = -0.4mV$$

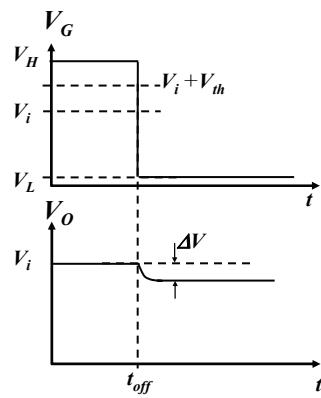
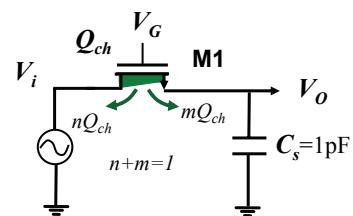


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Switch Charge Injection & Clock Feedthrough Fast Clock



- Sudden gate voltage drop \rightarrow no gate voltage to establish current in channel \rightarrow channel charge has no choice but to escape out towards S & D

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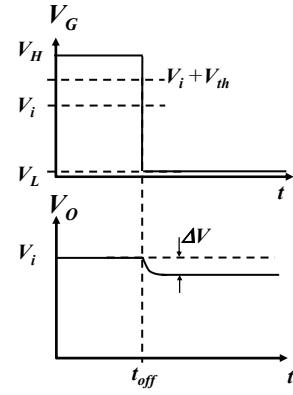
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Switch Charge Injection & Clock Feedthrough Fast Clock

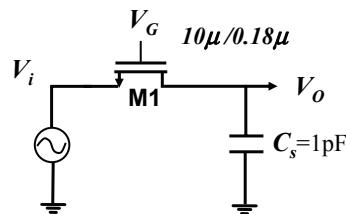
Clock Fall-Time << Device Speed:

$$\begin{aligned}\Delta V_o &= -\frac{C_{ov}}{C_{ov} + C_s}(V_H - V_L) - \frac{I}{2} \times \frac{Q_{ch}}{C_s} \\ &\approx -\frac{C_{ov}}{C_{ov} + C_s}(V_H - V_L) - \frac{I}{2} \times \frac{WC_{ox}L((V_H - V_i - V_{th}))}{C_s} \\ V_o &= V_i(1+\epsilon) + V_{os} \\ \text{where } \epsilon &= \frac{I}{2} \times \frac{WC_{ox}L}{C_s} \\ V_{os} &= -\frac{C_{ov}}{C_s}(V_H - V_L) - \frac{I}{2} \times \frac{WC_{ox}L(V_H - V_{th})}{C_s}\end{aligned}$$



- For simplicity it is assumed channel charge divided equally between S & D
- Source of error → channel charge transfer + clock feedthrough via C_{ov} to C_s

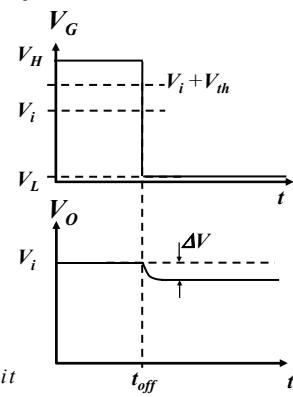
Switch Charge Injection & Clock Feedthrough Fast Clock- Example



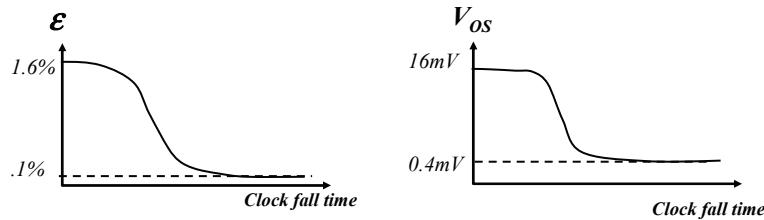
$$C_{ov} = 0.1 \frac{fF}{\mu}, C_{ox} = 9 \frac{fF}{\mu^2}, V_{th} = 0.4V, V_{DD} = 1.8V, V_L = 0$$

$$\epsilon = I/2 \frac{WLC_{ox}}{C_s} = \frac{10\mu \times 0.18\mu \times 9fF/\mu^2}{1pF} = 1.6\% \rightarrow \sim 5-bit$$

$$V_{os} = -\frac{C_{ov}}{C_s}(V_H - V_L) - \frac{I}{2} \times \frac{WC_{ox}L(V_H - V_{th})}{C_s} = -1.8mV - 14.6mV = -16.4mV$$



Switch Charge Injection & Clock Feedthrough Example-Summary



Error function of:

- Clock fall time
 - Input voltage level
 - Source impedance
 - Sampling capacitance size
 - Switch size
- ☞ Clock fall/rise should be controlled not to be faster (sharper) than necessary

Switch Charge Injection Error Reduction

- How do we reduce the error?
→ Reduce switch size to reduce channel charge?

$$\Delta V_o = -\frac{I}{2C_s} \frac{Q_{ch}}{C_s} \downarrow$$

$$\tau = R_{ON} C_s = \frac{C_s}{\mu C_{ox} \frac{W}{L} (V_{GS} - V_{th})} \uparrow \quad (\text{note: } \frac{T_s}{2} = k\tau)$$

Consider the figure of merit (FOM):

$$FOM = \frac{I}{\tau \times \Delta V_o} \approx \frac{\mu C_{ox} \frac{W}{L} (V_{GS} - V_{th})}{C_s} \times 2 \times \frac{C_s}{WC_{ox} L ((V_H - V_i - V_{th}))}$$

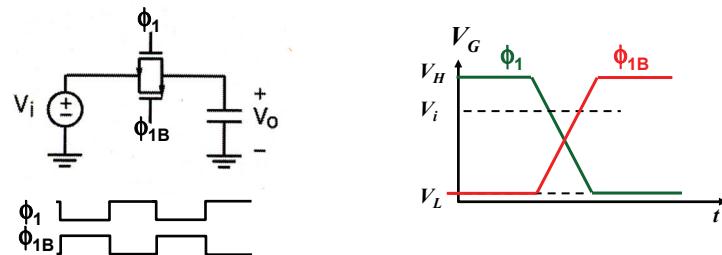
$$\rightarrow FOM \propto \mu / L^2$$

- ❖ Reducing switch size increases τ → increased distortion → not a viable solution
- ❖ Small τ and small ΔV → use minimum channel length (mandated by technology)
- ❖ For a given technology $\tau \times \Delta V \sim \text{constant}$

Sampling Switch Charge Injection & Clock Feedthrough Summary

- Extra charge injected onto sampling capacitor @ switch device turn-off
 - Channel charge injection
 - Clock feedthrough to C_s via C_{ov}
- Issues due to charge injection & clock feedthrough:
 - DC offset induced on hold C
 - Input dependant error voltage → distortion
- Solutions:
 - Slowing down clock edges as much as possible
 - Complementary switch?
 - Addition of dummy switches?
 - Bottom-plate sampling?

Switch Charge Injection & Clock Feedthrough Complementary Switch



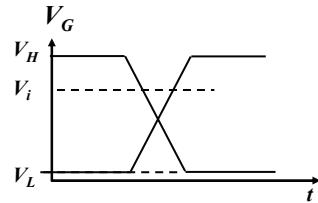
- In slow clock case if area of n & p devices & widths are equal ($W_n = W_p$) → effect of overlap capacitor for n & p devices to first order cancel (cancellation accuracy depends on matching of n & p width and overlap length L_D)
- Since in CMOS technologies $\mu_n \sim 2.5\mu_p$ choice of $W_n = W_p$ not optimal from linearity perspective ($W_p > W_n$ preferable)

Switch Charge Injection Complementary Switch Fast Clock

$$|Q_{ch-n}| = W_n C_{ox} L_n (V_H - V_i - |V_{th-n}|)$$

$$|Q_{ch-p}| = W_p C_{ox} L_p (V_i - V_L - |V_{th-p}|)$$

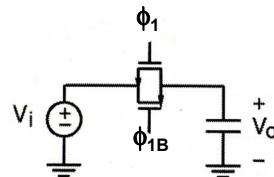
$$\Delta V_o \approx -\frac{1}{2} \left(\frac{|Q_{ch-n}|}{C_s} - \frac{|Q_{ch-p}|}{C_s} \right)$$



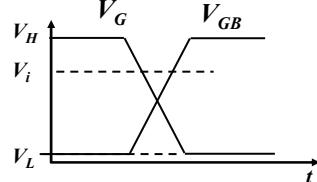
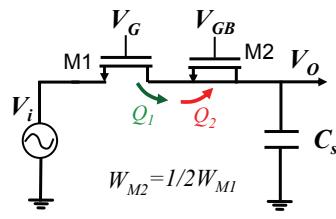
$$V_o = V_i (1 + \epsilon) + V_{os}$$

$$\epsilon \approx \frac{1}{2} \times \frac{W_n C_{ox} L_n + W_p C_{ox} L_p}{C_s}$$

- In fast clock case
 - To 1st order, offset due to overlap caps cancelled for equal device width
 - Input voltage dependant error worse!



Switch Charge Injection Dummy Switch

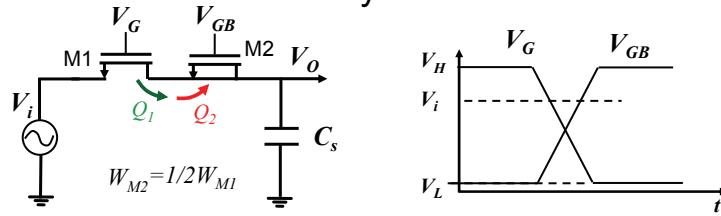


$$Q_l \approx \frac{1}{2} Q_{ch}^{M1} + Q_{ov}^{M1}$$

$$Q_2 \approx Q_{ch}^{M2} + 2Q_{ov}^{M2}$$

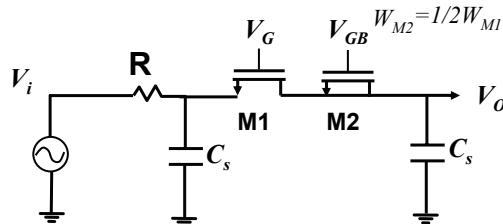
$$\text{For } W_{M2} = \frac{1}{2} W_{M1} \rightarrow Q_2 = -Q_l \quad \& \quad Q_{ov}^{M1} = 2Q_{ov}^{M2}$$

Switch Charge Injection Dummy Switch



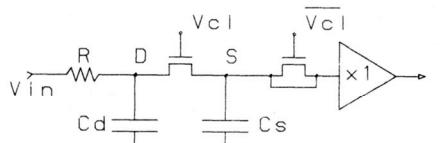
- Dummy switch same L as main switch but half W
- Main device clock goes low, dummy device gate goes high → dummy switch acquires same amount of channel charge main switch needs to lose
- Effective only if exactly half of the charge stored in M1 is transferred to M2 (depends on input/output node impedance) and requires good matching between clock fall/rise

Switch Charge Injection Dummy Switch



- To guarantee half of charge goes to each side → create the same environment on both sides
 - ❖ Add capacitor equal to sampling capacitor to the other side of the switch
 - + add fixed resistor to emulate input resistance of following circuit
 - Issues: Degrades sampling bandwidth

Dummy Switch Effectiveness Test



$R = 6K$ $C_s = C_d = 3pF$ $W/L = 18\mu m / 9\mu m$
 $V_{c1} = 15V$: fall, r_i set time = 20ns

V_{in}	UNCOMPENSATED SWITCH	COMPENSATED WITH DUMMY	BALANCED SWITCH
0v	-1.60mV	-45mV	6mV
5v	-1.05mV	-30mV	1mV
10v	-4.0mV	-11mV	0 ± 5mV

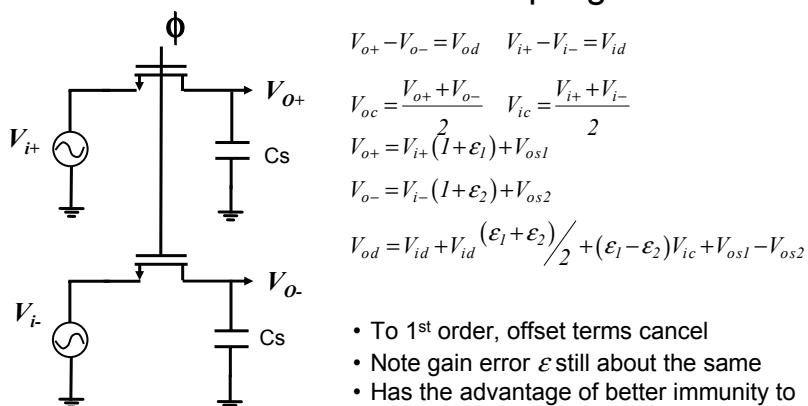
- Dummy switch
 $\rightarrow W = 1/2 W_{main}$

- As V_{in} is increased $V_{c1} - V_{in}$ is decreased \rightarrow channel charge decreased \rightarrow less charge injection

- Note large L_s \rightarrow good device area matching

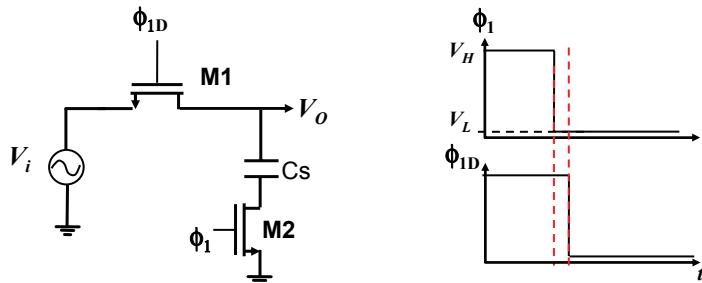
Ref: L. A. Bienstman et al, "An Eight-Channel 8 13bit Microprocessor Compatible NMOS D/A Converter with Programmable Scaling", IEEE JSSC, VOL. SC-15, NO. 6, DECEMBER 1980

Switch Charge Injection Differential Sampling



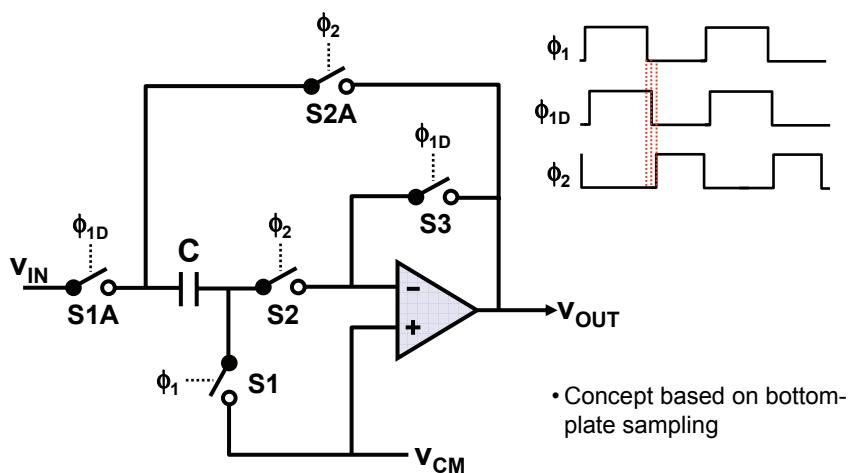
- To 1st order, offset terms cancel
- Note gain error ϵ still about the same
- Has the advantage of better immunity to noise coupling and cancellation of even order harmonics

Avoiding Switch Charge Injection Bottom Plate Sampling



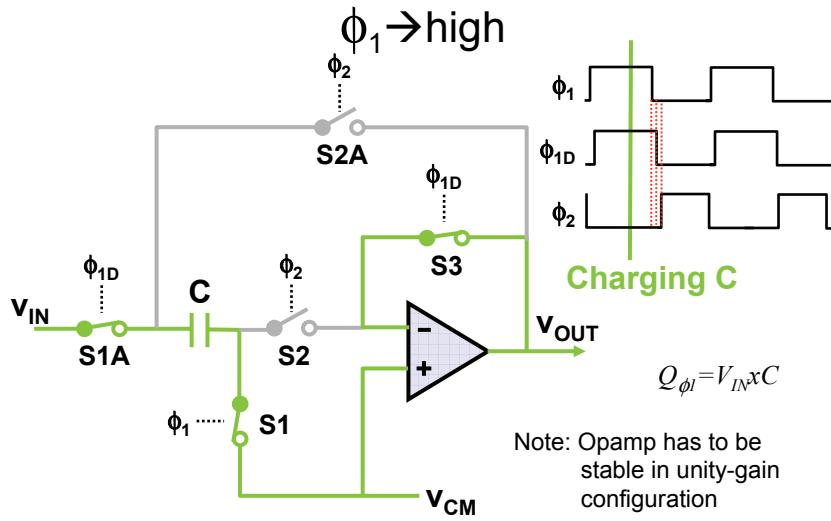
- Switches M_2 opened slightly earlier compared to M_1
→ Injected charge by the opening of M_2 is constant since its GS voltage is constant & eliminated when used differentially
- Since C_s bottom plate is already open when M_1 is opened
→ No signal dependant charge injected on C_s

Flip-Around Track & Hold



- Concept based on bottom-plate sampling

Flip-Around T/H-Basic Operation

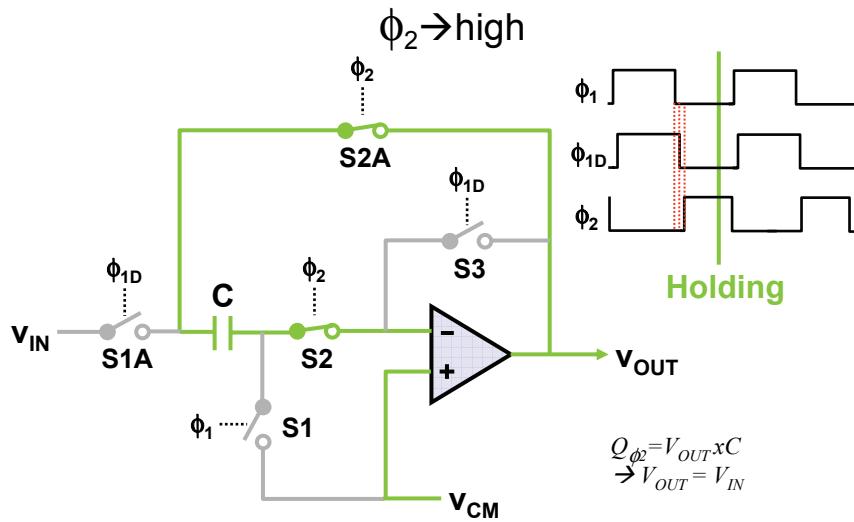


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Flip-Around T/H-Basic Operation

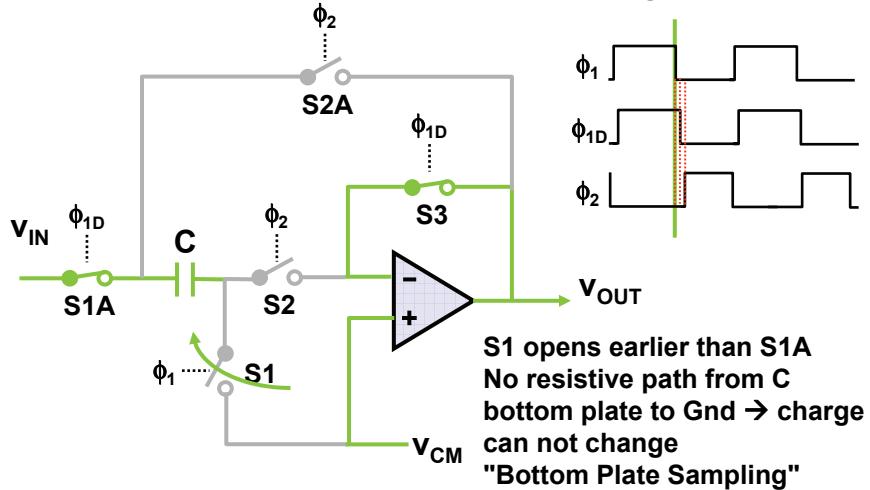


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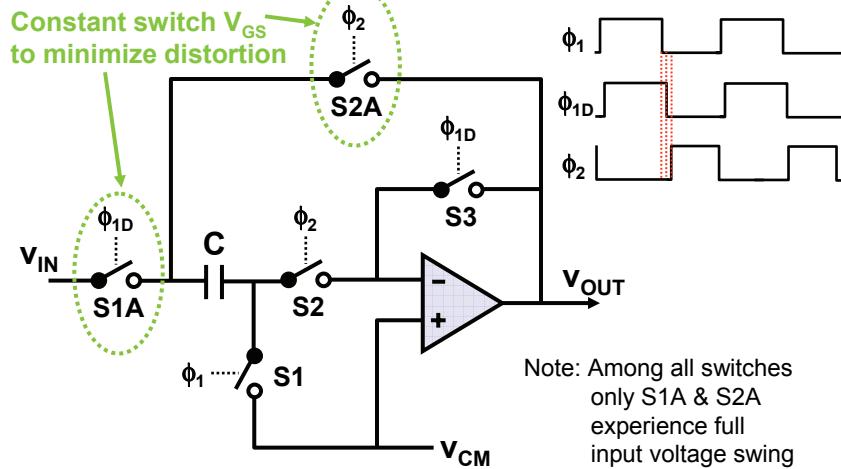
Flip-Around T/H - Timing



Charge Injection

- At the instant of transitioning from track to hold mode, some of the charge stored in sampling switch $S1$ is dumped onto C
- With "Bottom Plate Sampling", only charge injection component due to opening of $S1$ and is to first-order independent of V_{IN}
 - Only a dc offset is added. This dc offset can be removed with a differential architecture

Flip-Around T/H



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Flip-Around T/H

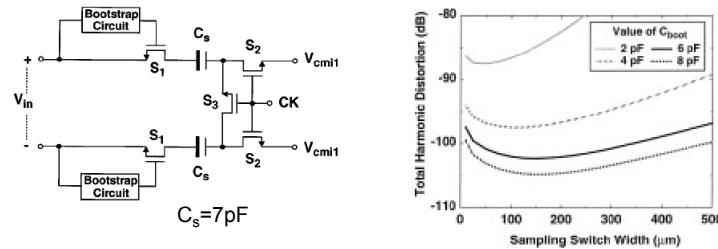
- S1 is chosen to be an n-channel MOSFET
- Since it always switches the same voltage, its on-resistance, R_{S1} , is signal-independent (to first order)
- Choosing $R_{S1} \gg R_{S1A}$ minimizes the non-linear component of $R = R_{S1A} + R_{S1}$
 - Typically, S1A is a wide (much lower resistance than S1) & constant V_{GS} switch
 - In practice size of S1A is limited by the (nonlinear) S/D capacitance that also adds distortion
 - If S1A's resistance is negligible \rightarrow delay depends only on S1 resistance
 - S1 resistance is independent of V_{IN} \rightarrow error due to finite time-constant \rightarrow independent of V_{IN}

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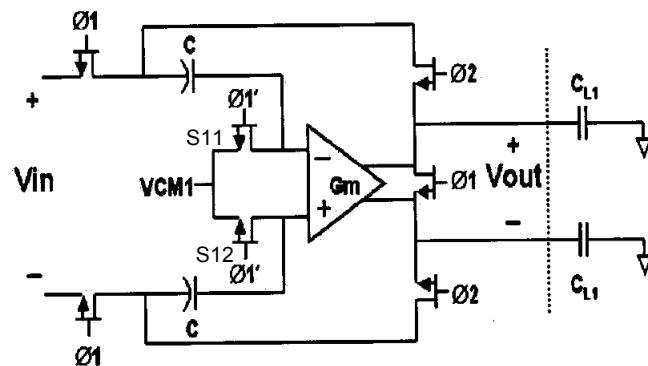
Differential Flip-Around T/H Choice of Sampling Switch Size



- THD simulated w/o sampling switch boosted clock $\rightarrow -45\text{dB}$
- THD simulated with sampling switch boosted clock (see graph)

Ref: K. Vleugels et al, "A 2.5-V Sigma-Delta Modulator for Broadband Communications Applications" IEEE JSSC, VOL. 36, NO. 12, DECEMBER 2001, pp. 1887

Differential Flip-Around T/H

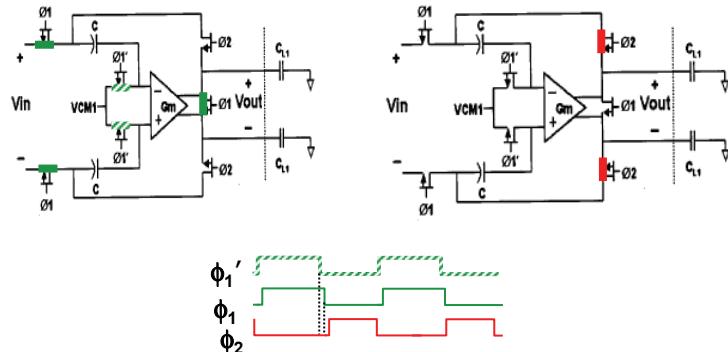


Offset voltage associated with charge injection of S_{11} & S_{12} cancelled by differential nature of the circuit

During input sampling phase \rightarrow amp outputs shorted together

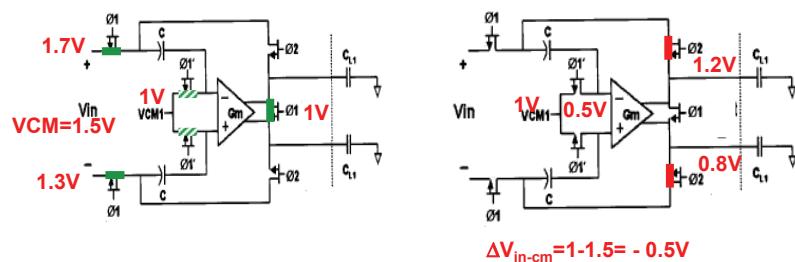
Ref: W. Yang, et al. "A 3-V 340-mW 14-b 75-Msample/s CMOS ADC With 85-dB SFDR at Nyquist Input," IEEE JOURNAL OF SOLID-STATE CIRCUITS, VOL. 36, NO. 12, DECEMBER 1991

Differential Flip-Around T/H



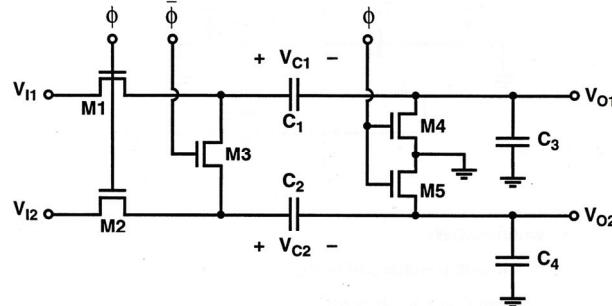
- Gain=1
- Feedback factor=1

Differential Flip-Around T/H Issues: Input Common-Mode Range



- $\Delta V_{in_cm} = V_{out_com} - V_{sig_com}$
- Amplifier needs to have large input common-mode compliance

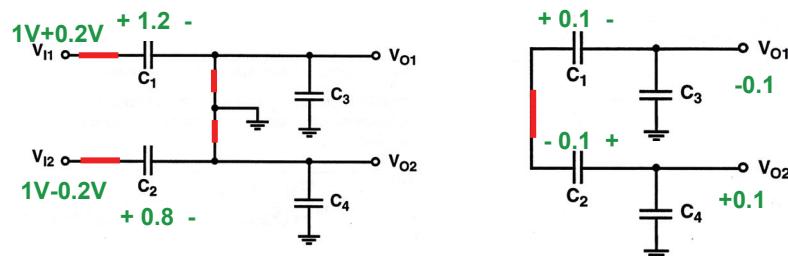
Input Common-Mode Cancellation



- Note: Shorting switch M3 added

Ref: R. Yen, et al. "A MOS Switched-Capacitor Instrumentation Amplifier," IEEE JOURNAL OF SOLID-STATE CIRCUITS, VOL. SC-17, NO. 6., DECEMBER 1982 1008

Input Common-Mode Cancellation



Track mode (ϕ high)
 $V_{C1}=V_{I1}$, $V_{C2}=V_{I2}$
 $V_{O1}=V_{O2}=0$

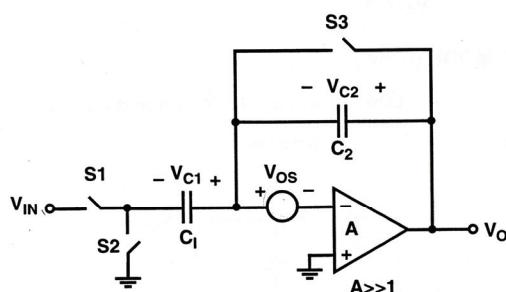
Hold mode (ϕ low)
 $V_{O1}+V_{O2}=0$
 $V_{O1}-V_{O2}=-(V_{I1}-V_{I2})(C_1/(C_1+C_3))$

→ Input common-mode level removed

Switched-Capacitor Techniques Combining Track & Hold with Other Functions

- T/H + Charge redistribution amplifier
- T/H & Input difference amplifier
- T/H & summing amplifier
- Differential T/H combined with gain stage
- Differential T/H including offset cancellation

T/H + Charge Redistribution Amplifier



Track mode: ($S_1, S_3 \rightarrow$ on $S_2 \rightarrow$ off)

$$V_{C1} = V_{os} - V_{IN}, \quad V_{C2} = 0$$
$$V_o = V_{os}$$

T/H + Charge Redistribution Amplifier Hold Mode

$$V_{C1} \rightarrow V_{os}$$

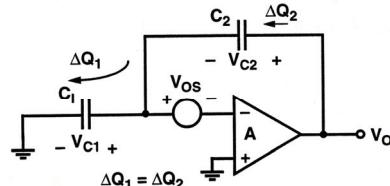
$$\Delta V_{C1} = V_{os} - (V_{os} - V_{IN}) = V_{IN}$$

$$\Delta Q_1 = C_1 \Delta V_{C1} = C_1 V_{IN}$$

$$\Delta Q_2 = C_2 \Delta V_{C2} = \Delta Q_1$$

$$\Delta V_{C2} = \left(\frac{C_1}{C_2}\right) V_{C1} = V_{C2}$$

$$V_o = V_{C2} + V_{os} = \left(\frac{C_1}{C_2}\right) V_{IN} + V_{os}$$

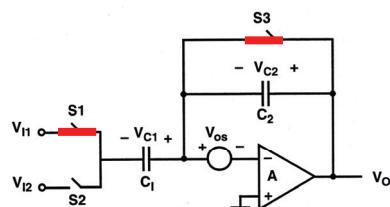
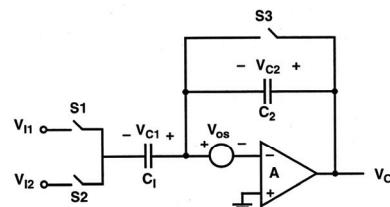


Hold/amplify mode (S1, S3 → off S2 → on)

→ Offset NOT cancelled, but not amplified

→ Input-referred offset = $(C_2/C_1) \times V_{os}$, & often $C_2 < C_1$

T/H & Input Difference Amplifier



Sample mode:
(S1, S3 → on S2 → off)
 $V_{C1} = V_{os} - V_{I1}$, $V_{C2} = 0$
 $V_o = V_{os}$

Input Difference Amplifier Cont'd

Subtract/Amplify mode (S1, S3 → off S2 → on)

During previous phase:

$$V_{C1} = V_{os} - V_{I1}, \quad V_{C2} = 0$$

$$V_o = V_{os}$$

$$V_{C1} = V_{os} - V_{I2}$$

$$\Delta V_{C1} = (V_{os} - V_{I2}) - (V_{os} - V_{I1}) = V_{I1} - V_{I2}$$

$$\Delta V_{C2} = \left(\frac{C_1}{C_2}\right) \Delta V_{C1} = \left(\frac{C_1}{C_2}\right) (V_{I1} - V_{I2})$$

$$V_o = \left(\frac{C_1}{C_2}\right) (V_{I1} - V_{I2}) + V_{os}$$

→ Offset NOT cancelled, but not amplified

→ Input-referred offset = $(C_2/C_1) \times V_{os}$, & $C_2 < C_1$

